



Docket No.: M4065.0700/P700-A  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Terry L. Gilton, et al.

Application No.: 10/634,897

Filed: August 6, 2003

Art Unit: N/A

For: METHODS OF FORMING NON-VOLATILE RESISTANCE VARIABLE DEVICES AND METHODS OF FORMING SILVER SELENIDE COMPRISING STRUCTURES

Examiner: Not Yet Assigned

**INFORMATION DISCLOSURE STATEMENT (IDS)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed within three months of the U.S. filing date (37 CFR 1.97(b)(1)).

Those patent(s) or publication(s) which are marked with an asterisk (\*) next to the Cite No. in the attached form PTO/SB/08 are not supplied because they were previously cited by or submitted to the Office in a prior application number 10/061,825, filed January 31, 2002 and relied upon in this application for an earlier filing date under 35 U.S.C. 120.

A concise explanation of relevance of the items not marked by asterisk and listed on form PTO/SB/08 is in the form of an English language copy of a Search Report from a foreign patent office, issued in a counterpart application, which refers to the relevant portions of the references.

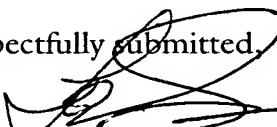
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It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0700/P700-A. A duplicate copy of this paper is enclosed.

Dated: November 5, 2003

Respectfully submitted,

By   
Thomas J. D'Amico

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PTO/SB/08a/b (08-03)

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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(Use as many sheets as necessary)*

Sheet	1	of	11	Attorney Docket Number	M4065.0700/P700-A
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### *C mplete if Known*

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First Named Inventor	Terry L. Gilton
Art Unit	N/A
Examiner Name	Not Yet Assigned

### U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
AA	US-6,117,720	09/12/2000	Harshfield		
AB	US-3,450,967	06/17/1969	Tolutis		
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*	p	US-2003/0027416 APP	2/6/2003	Moore
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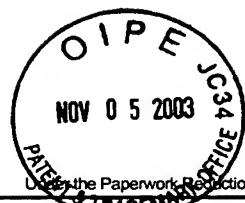
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*	A29	US-5,512,328	04/1996	Yoshimura et al.	
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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
	BA	WO 97/48032	12/18/1997	Kozicki et al.		
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NON PATENT LITERATURE DOCUMENTS						
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T <sup>2</sup>
*	CA	G. SAFRAN, "Development and properties of single-crystal silver selenide layers," <i>Thin Solid Films</i> , 215 (1992) 147-151.				
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Sheet

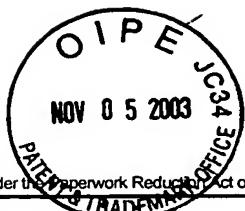
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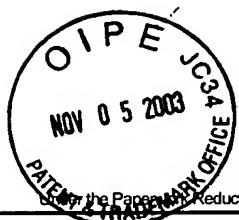
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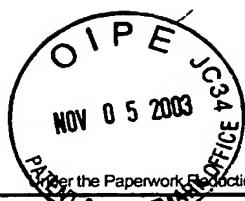
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